





#### **50V NPN LOW SATURATION TRANSISTOR**

#### **Features and Benefits**

- BV<sub>CEO</sub> > 50V
- I<sub>C</sub> = 4A Continuous Collector Current
- Low Saturation Voltage (100mV max @ 1A)
- R<sub>SAT</sub> = 68 mΩ for a low equivalent On-Resistance
- hFE specified up to 6A for high current gain hold up
- Low profile 0.6mm high package for thin applications
- R<sub>0</sub>JA efficient, 60% lower than SOT23
- 4mm<sup>2</sup> footprint, 50% smaller than SOT23
- Lead-Free, RoHS Compliant (Note 1)
- Halogen and Antimony Free. "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: DFN2020B-3
- Case Material: Molded Plastic. "Green" Molding Compound.
- Terminals: Pre-Plated NiPdAu leadframe.
- Nominal Package Height: 0.6mm
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Weight: 0.01 grams (approximate)

### **Applications**

- MOSFET Gate Driving
- DC-DC Converters
- Charging circuits
- Motor Control
- Power switches

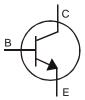
#### DFN2020B-3



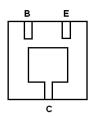




**Bottom View** 



Device Symbol



Bottom View Pin-Out

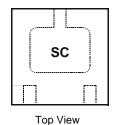
## **Ordering Information**

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTN619MATA	SC	7	8	3000

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com

## **Marking Information**



SC = Product Type Marking code





# Maximum Ratings @TA = 25°C unless otherwise specified

Parameter		Symbol	Limit	Unit	
Collector-Base Voltage		V <sub>CBO</sub>	100		
Collector-Emitter Voltage		V <sub>CEO</sub>	50	V	
Emitter-Base Voltage		V <sub>EBO</sub>	7		
Peak Pulse Current		I <sub>CM</sub>	6		
Continuous Collector Current	(Note 3)	_	4	1	
	(Note 4)	IC	4.3	] ^	
Base Current		I <sub>B</sub>	1		

# Thermal Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 3)		1.5 12	W	
Linear Derating Factor	(Note 4)	P <sub>D</sub>	2.45 19.6	mW/°C	
Thermal Resistance, Junction to Ambient	(Note 3)	Б	83		
mermal Resistance, Junction to Ambient	(Note 4)	$-$ R <sub><math>\theta</math>JA</sub>	51	°C/W	
Thermal Resistance, Junction to Lead (Note 5)		$R_{ hetaJL}$	16.8		
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C		

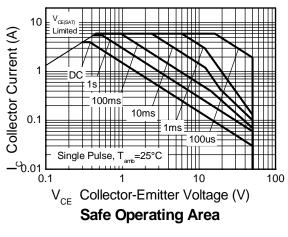
Notes:

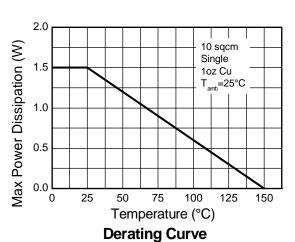
For a device surface mounted on 31mm x 31mm (10cm²) FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition. The entire exposed collector pad is attached to the heatsink.
Same as note (3), except the device is measured at t ≤ 5 sec.

<sup>5.</sup> For a single device, thermal resistance from junction to solder-point (at the end of the drain lead).

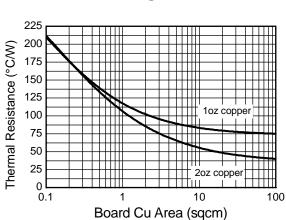


### **Thermal Characteristics**

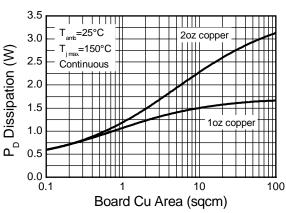




# 80 10 sqcm Single 10z Cu D=0.5 Single Pulse D=0.05 D=0.05



### **Transient Thermal Impedance**



Thermal Resistance v Board Area

Power Dissipation v Board Area





## Electrical Characteristics @TA = 25°C unless otherwise specified

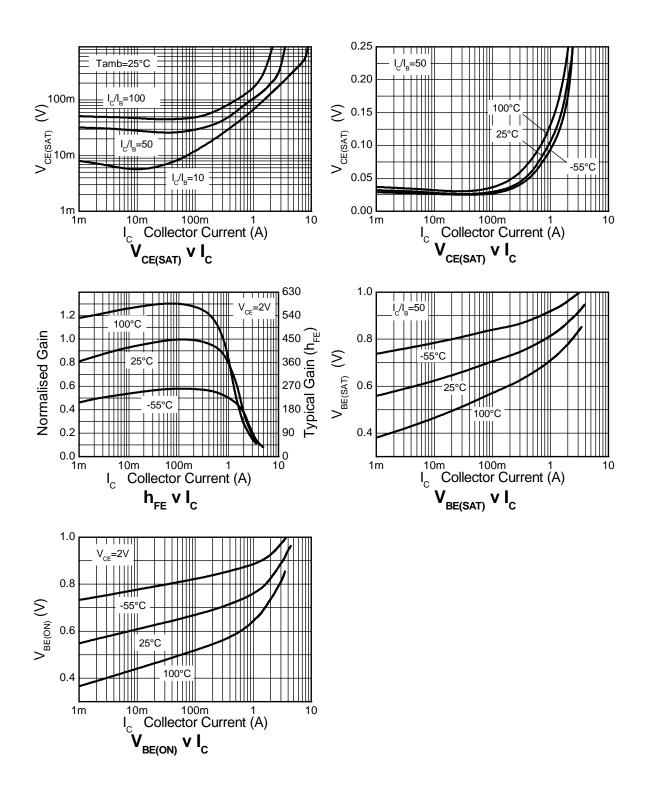
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	100	190	-	V	I <sub>C</sub> = 100 μA
Collector-Emitter Breakdown Voltage (Note 6)	BV <sub>CEO</sub>	50	65	-	V	I <sub>C</sub> = 10 mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	7	8.2	-	V	I <sub>E</sub> = 100 μA
Collector Cutoff Current	I <sub>CBO</sub>	-	-	100	nA	V <sub>CB</sub> = 80V
Emitter Cutoff Current	I <sub>EBO</sub>	-	-	100	. nA	V <sub>EB</sub> = 6V
Collector Emitter Cutoff Current	I <sub>CES</sub>	-	-	100	nA	V <sub>CES</sub> = 40V
Static Forward Current Transfer Ratio (Note 6)	hFE	200 300 200 100	400 450 400 225 40	- - - -	-	$I_{C} = 10$ mA, $V_{CE} = 2$ V $I_{C} = 200$ mA, $V_{CE} = 2$ V $I_{C} = 1$ A, $V_{CE} = 2$ V $I_{C} = 2$ A, $V_{CE} = 2$ V $I_{C} = 6$ A, $V_{CE} = 2$ V
Collector-Emitter Saturation Voltage (Note 6)	V <sub>CE</sub> (sat)		10 70 145 115 225 270	20 100 200 220 300 320	mV	$\begin{split} I_C &= 0.1A, \ I_B = 10 mA \\ I_C &= 1A, \ I_B = 5 mA \\ I_C &= 1A, \ I_B = 10 mA \\ I_C &= 2A, \ I_B = 50 mA \\ I_C &= 3A, \ I_B = 100 mA \\ I_C &= 4A, \ I_B = 200 mA \end{split}$
Base-Emitter Turn-On Voltage (Note 6)	V <sub>BE(on)</sub>	-	0.94	1.00	V	I <sub>C</sub> = 4A, V <sub>CE</sub> = 2V
Base-Emitter Saturation Voltage (Note 6)	V <sub>BE(sat)</sub>	-	1.00	1.07	V	I <sub>C</sub> = 4A, I <sub>B</sub> = 200mA
Output Capacitance	C <sub>obo</sub>	-	12	20	pF	V <sub>CB</sub> = 10V. f = 1MHz
Transition Frequency	f <sub>T</sub>	100	165	-	MHz	V <sub>CE</sub> = 10V, I <sub>C</sub> = 50mA, f = 100MHz
Turn-On Time	t <sub>on</sub>	-	170	-	ns	V <sub>CC</sub> = 10V, I <sub>C</sub> = 1A
Turn-Off Time	t <sub>off</sub>	-	750	-	ns	$I_{B1} = I_{B2} = 10 \text{mA}$

Notes: 6. Measured under pulsed conditions. Pulse width  $\leq$  300  $\mu$ s. Duty cycle  $\leq$  2%.



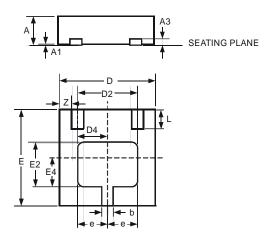


## **Typical Electrical Characteristics**



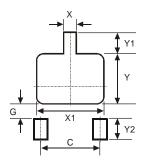


# **Package Outline Dimensions**



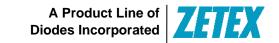
DFN2020B-3						
Dim	Min	Max	Тур			
<b>A</b> 0.57		0.63	0.60			
A1	0	0.05	0.02			
A3		_	0.152			
b	0.20	0.30	0.25			
D	1.95	2.075	2.00			
D2	1.22	1.42	1.32			
D4	0.56	0.76	0.66			
е		_	0.65			
Е	1.95	2.075	2.00			
E2	0.79	0.99	0.89			
E4	0.48	0.68	0.58			
L	0.25	0.35	0.30			
Z		_	0.225			
All Dimensions in mm						

# **Suggested Pad Layout**



Dimensions	Value (in mm)
С	1.30
G	0.24
Х	0.35
X1	1.52
Υ	1.09
Y1	0.47
Y2	0.50





#### **IMPORTANT NOTICE**

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

#### LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
  - 1. are intended to implant into the body, or
  - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2011, Diodes Incorporated

www.diodes.com